

PRESIDENCY UNIVERSITY

# Mid - Term Examinations - November 2024

Semester: V Date: 04/11/2024 Course Code: ECE3008 Time: 09.30am to 11.00am Course Name: VLSI Design Max Marks: 50 Program: B.Tech Weightage: 25%

## **Instructions:**

(i) Read all questions carefully and answer accordingly.

(ii) Do not write anything on the question paper other than roll number.

Part A

Answer ALL the Questions. Each question carries 2marks.			5QX2M=10M		
1	What's the relationship between the drain and current in the MOSFET as a function of gate-to-source voltage and drain to source voltage?	2 Marks	L1	C01	
2	Define MOS diode and mention at least two applications.	2 Marks	L1	C01	
3	Define Substrate Bias effect.	2 Marks	L1	CO2	
4	The current conduction in the channel is in the form of drift. If the mobility falls at high temperatures, what can we say about the on-resistance as the temperature goes up?	2 Marks	L1	CO2	
5	Identify the region of operation of transistor M1 and M2	2 Marks	L1	CO1,2	
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Answer ALL Questions. Each question carries 10 marks.

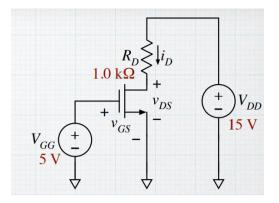
### Part B

#### MOS transistor switches ON when a proper voltage is applied at 6 6 Marks C01 a. L3 the gate terminal. Calculate the current flow in the NMOS with

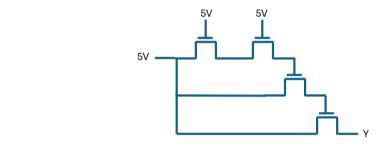
## 4QX10M=40M

 $2.5V \longrightarrow M_2$   $2V \longrightarrow M_1$ 

		the following parameters. L= 2µm. W =10 µm, µ <sub>n</sub> = $0.05m^2/v$ -s, Cox = $1.5 * 10^{-4}$ F/m2, VT = $0.4$ V.			
		i). VGS = $0.45v$ , VDS = $0V$			
		ii). VGS = 0.8 v, VDS = 0.4 V			
	b.	Identify the region of operation for each case.	4 Marks	L1	C01
		or			
7		The active load is used in n-MOSFET inverter to reduce the area of the chip. Derive small signal gain and output resistance of n- MOSFET inverter with active load.	10 Marks	L3	C01
8	a.	The metal oxide semiconductor transistor or MOS transistor is a basic building block in logic chips, processors & modern digital memories. Explain the operation for NMOS transistor in different regions (Cut-off, Linear and Saturation regions).	6 Marks	L2	C01
	b.	Plot the ID-VDS and ID-VGS characteristics for different values of VGS and VDS respectively.	4 Marks	L2	C01
		or			
	a.	NMOS transistors operate by creating an inversion layer in a p- type transistor body. Define channel length modulation?	3 Marks	L1	C01
9	b.	The current flowing through an NMOS (n-channel metal-oxide- semiconductor) transistor can be described by the basic equation. Derive drain current equation assuming channel length modulation.	7 Marks	L3	C01
10	a.	Discuss small signal equivalent circuit model of MOSFET without considering the effect of channel length modulation modelled by output resistance.	5 Marks	L2	C02
	b.	Summarize important Design techniques you would follow when doing a Layout for Digital Circuits?	5 Marks	L2	CO2
		or			
11	a.	NMOS is like a regular switch - applying a voltage (like flipping the switch) turns it on, allowing current (like light) to flow. For the circuit shown, use the the NMOS equations to find ID and VDS.	7 Marks	L3	CO2



- **b.** Why is the substrate in NMOS connected to Ground and in PMOS 3 Marks L2 CO2 to VDD?
- a. Stick diagrams are a means of capturing topography and layer 6 Marks L2 CO2 information using simple diagrams. Draw the transistor level schematic (CMOS) and stick diagram for 3 input NAND gate
- **b.** For the given circuit, if the threshold voltage of each transistor is 4 Marks L2 CO2 0.5V, then what is the output voltage at node Y.



or

- a. Stick diagrams are used to represent VLSI layouts in an abstract 6 Marks L2 CO2 way, showing the relative placements and connections between different layers like polysilicon, diffusion, and metal layers. Draw the transistor level schematic (CMOS) and stick diagram for 3 input NOR gate
- **b.** Find out the voltage at P, Q, R for given NMOS transistor. Assume 4 Marks L2 CO2 Vt=1V.

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